Takanori Asano

List of Publications by Year in descending order

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1163117 1372567 10 128 8 10 citations h-index g-index papers 10 10 10 119 docs citations times ranked citing authors all docs

#	Article	IF	CITATIONS
1	Experimental observation of type-I energy band alignment in lattice-matched Gelâ^' <i>x</i> â^' <i>y</i> Si <i>x</i> Solicity	3.3	23
2	Non-uniform depth distributions of Sn concentration induced by Sn migration and desorption during GeSnSi layer formation. Applied Physics Letters, 2015, 106, .	3.3	20
3	Influence of Sn incorporation and growth temperature on crystallinity of $Ge1\hat{a}^2xSnx$ layers heteroepitaxially grown on $Ge(110)$ substrates. Thin Solid Films, 2013, 531, 504-508.	1.8	18
4	Crystallinity Improvement of Epitaxial Ge Grown on a $Ge(110)$ Substrate by Incorporation of Sn. Applied Physics Express, 2012, 5, 015501.	2.4	14
5	Influence of Ge substrate orientation on crystalline structures of Ge1â^'Sn epitaxial layers. Thin Solid Films, 2014, 557, 159-163.	1.8	14
6	Epitaxial growth and crystalline properties of Ge1 $\hat{a}^{\hat{a}}$ 3 $\hat{a}^{\hat{a}}$ Si Sn on Ge(0 0 1) substrates. Solid-State Electronics, 2015, 110, 49-53.	1.4	14
7	Epitaxial growth and anisotropic strain relaxation of Ge1â^'xSnx layers on Ge(110) substrates. Solid-State Electronics, 2013, 83, 71-75.	1.4	11
8	Formation and characterization of Ge $1\hat{a}^2\hat{x}\hat{a}^2\hat{y}$ Si x Sn y /Ge $1\hat{a}^2\hat{x}$ Sn x /Ge $1\hat{a}^2\hat{x}\hat{a}^2\hat{y}$ Si x Sn y double heterostructures with strain-controlled Ge $1\hat{a}^2\hat{x}\hat{a}^2\hat{y}$ Si x Sn y layers. Materials Science in Semiconductor Processing, 2017, 70, 156-161.	4.0	9
9	Defect and dislocation structures in low-temperature-grown Ge and Ge1â^'Sn epitaxial layers on Si(110) substrates. Thin Solid Films, 2016, 598, 72-81.	1.8	3
10	Formation of high-quality Ge1â^'xSnx layer on Ge(110) substrate with strain-induced confinement of stacking faults at Ge1â^'xSnx/Ge interfaces. Applied Physics Express, 2014, 7, 061301.	2.4	2